

## REMARKS

Claim 7 has been amended to include the subject matter of former claim 8. Claim 8 was rejected under Section 102 based on Hwu. However, it is not specifically pointed out in the office action where a liquid oxidizer is used. To the contrary, electrical current is used as the oxidation mechanism in Hwu. No liquid oxidizer is utilized because electricity is used instead.

With the present invention, the use of a liquid oxidizer, such as the liquid oxidizer set forth in claim 13, results in less under layer of oxide being formed between the metallic oxide and the substrate.

While the use of liquid oxidizers is known, the use of liquid oxidizers to oxidize a precursor directly formed on a semiconductor substrate to avoid an under layer being formed is not taught in any of the cited references. Note that in the cited reference to Tsuzumitani, titanium is formed on a third interlayer dielectric film 5. The metal layer 7a is then oxidized. However, the layer 7a is never formed directly on the substrate. Therefore, the problem with forming an intermediate layer of oxide between the metal layer and the substrate does not arise. Tsuzumitani cannot teach that the way to overcome this layer is to use a liquid oxidizer, in the case of claim 1, and the specific mild oxidizer set forth in claim 13.

Therefore, reconsideration of the rejections of claims 7 and 13 is respectfully requested.

Respectfully submitted,

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